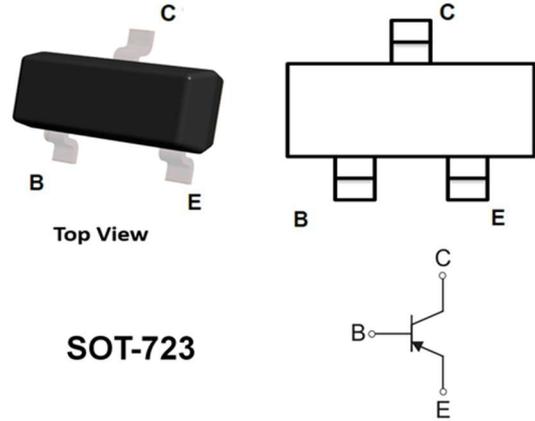# MMBT3906M

MMBT3906M
PNP General Purpose Transistor

General description
• PNP General Purpose Transistor

FEATURES
• SOT-723 General Purpose Transistors.
• VCEO   -40V
• Ic   -200mA
• PC   100mW
• Complementary to MMBT3904M
• Small Outline Surface Mount Package.
• RoHS Compliant / Green EMC.

Type	MMBT3904M
Marking	3N

Top View

SOT-723

Absolute Maximum Ratings(Ta=25℃)

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current -Continuous	I_C	-0.2	A
Power Dissipation	P_C	0.1	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	1250	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55～+150	℃

MMBT3906M

ELECTRICAL CHARACTERISTICS @ 25°C Unless Otherwise Specified

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=10μA,I_E=0	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	-40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA,I_C=0	-5			V
Collector cut-off current	I_{CEX}	V_{CE}=-30V,$V_{EB(off)}$=-3V			-50	nA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V,I_C=0			-100	nA
DC current gain	h_{FE}	V_{CE}=-1V,I_C=-0.1mA	40			
		V_{CE}=-1V,I_C=-1mA	70			
		V_{CE}=-1V,I_C=-10mA	100		300	
		V_{CE}=-1V,I_C=-50mA	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-10mA,I_B=-1mA			-0.2	V
		I_C=-50mA,I_B=-5mA			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-10mA,I_B=-1mA	-0.65		-0.85	V
		I_C=-50mA,I_B=-5mA			-0.95	V
Transition frequency	f_T	V_{CE}=-20V,I_C=-10mA,f=100MHz	300			MHz
Output capacitance	C_{ob}	V_{CB}=-5V,I_E=0,f=1MHz			4	pF
Input capacitance	C_{ib}	V_{EC} =-0.5V,I_C=0,f=1MHz			8	pF
Noise figure	NF	V_{CE}=-5V,I_C=-0.1mA,f=1MHz,R_S=1kΩ			5	dB

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Delay time	t_d	V_{CC}=-3V,$V_{BE(off)}$=-0.5V, I_C=-10mA,I_{B1}=-1mA			35	ns
Rise time	t_r				25	ns
Storage time	t_s	V_{CC}=-3V,I_C=-10mA I_{B1}=I_{B2}=-1mA			225	ns
Fall time	t_f				75	ns

TYPICAL CHARACTERICTIC

Static Characteristic

h_{FE} — I_C

V_{CEsat} — I_C

V_{BEsat} — I_C

I_C — V_{BE}

C_{ob}/C_{ib} — V_{CB}/V_{EB}
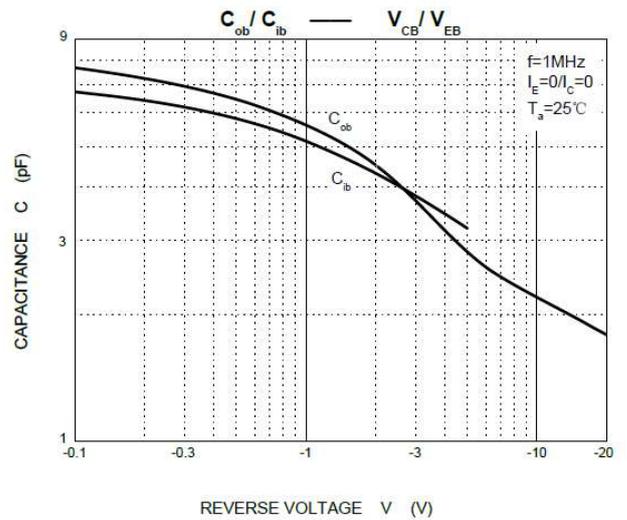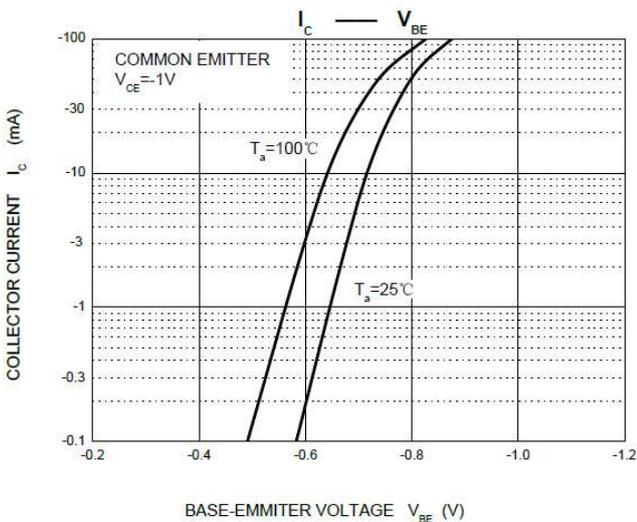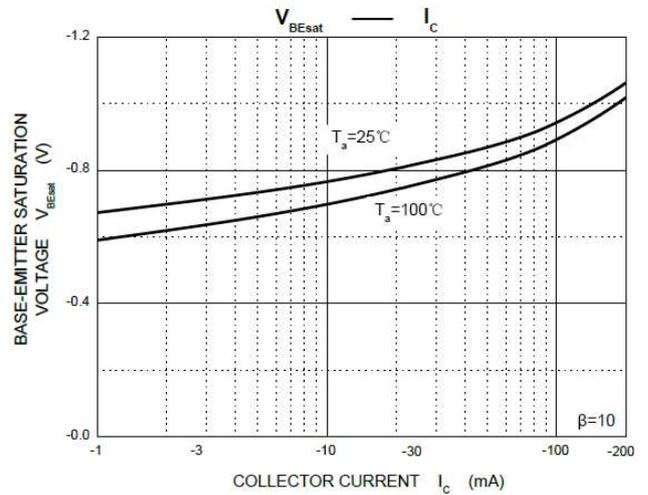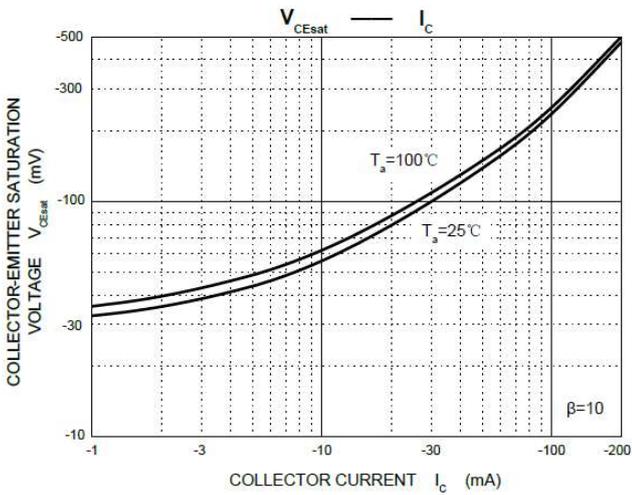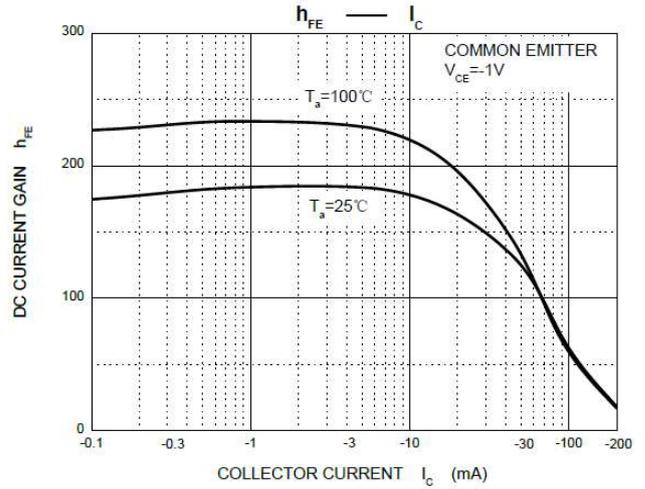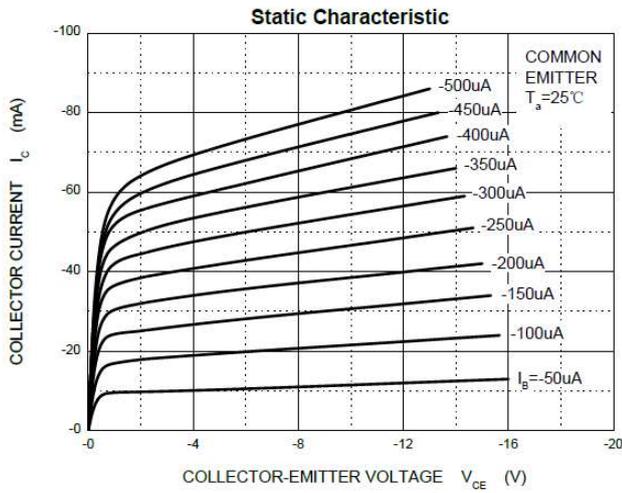
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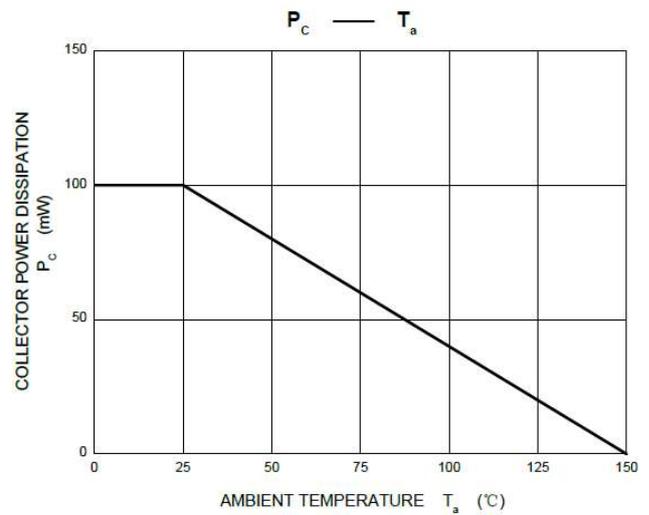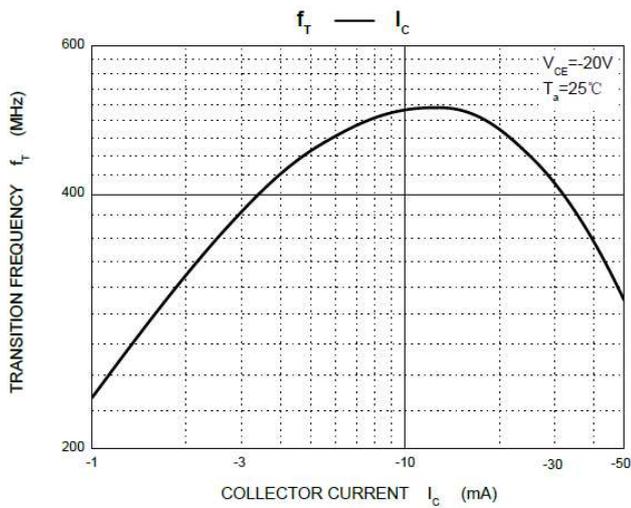
PACKAGE DIMENSIONS
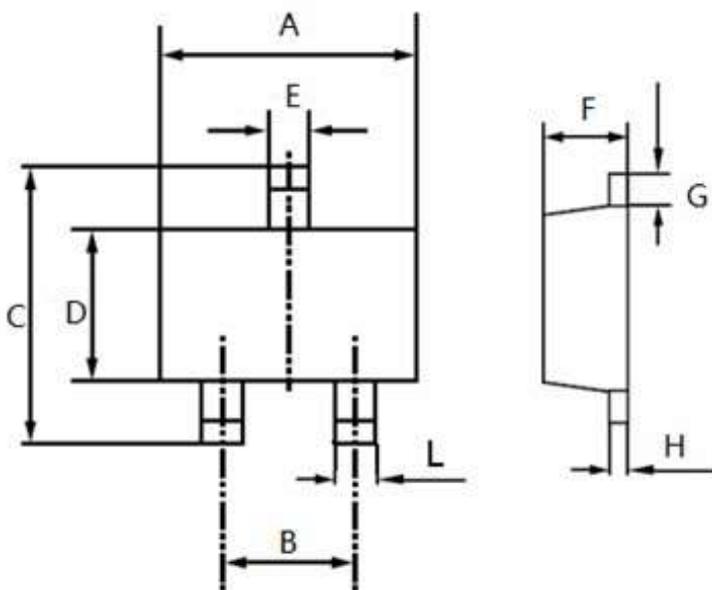
Symbol	Dimensions In Millimeters	
	Min	Max
A	1.100	1.300
B	0.8typ	
C	1.100	1.300
D	0.700	0.900
E	0.200	0.300
F	0.400	0.500
G	0.150	0.250
H	0.060	0.160
L	0.150	0.250

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